

FORM PTO-1449

U.S. Department of Commerce  
Patent and Trademark OfficeAtty. Docket No.  
FIS920030232US1Application No.  
10/707,996INFORMATION DISCLOSURE STATEMENT  
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Applicant  
Daniel C. EDELSTEIN et al.Filing Date  
01/30/2004Group  
2813

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

## FOREIGN PATENT DOCUMENTS

DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO
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## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>Ar</i>		V. Arnal, et al., "A Novel SiO <sub>2</sub> Air Gap Low K for Copper Dual Damascene Interconnect." Conference Proceedings of the Advanced Metallization Conference 2000, pp. 71-76
		A. P. Li, et al., "Hexagonal Pore Arrays with a 50-420 nm Interpore Distance Formed by Self-Organization in Anodic Alumina." Journal of Applied Physics, vol. 84, no. 11, December 1, 1998, pp. 6023-6026
		O. Jessensky, et al., "Self-Organization Formation of Hexagonal Pore Arrays in Anodic Alumina." Journal of Applied Physics, vol. 72, no. 10, March 9, 1998, pp. 1173-1175.
		A. P. Li, et al., "Polycrystalline Nanopore Arrays with Hexagonal Ordering on Aluminum." Journal of Vacuum Science and Technology, vol. 17, no. 4, July/August 1999, pp. 1428-1431.
		L.G. Gosset, et al., "General Review of Issues and Perspectives for Advanced Copper Interconnections Using Advanced Copper Interconnections Using Air Gaps as Ultra-Low K Material." IEEE 2003, pp. 65-67.
		V. Arnal, et al., "Integration of a 3 Level Cu - SiO <sub>2</sub> Air Gap Interconnect for Sub 0.1 micron CMOS Technologies." IEEE 2001, pp. 298-300.
<i>U</i>		C.T. Black, et al., "Integration of Self-Assembled Diblock Copolymers for Semiconductor Capacitor Fabrication." Applied Physics Letters, vol. 79, no. 3, July 16, 2001, pp.409-411
<i>Ar</i>		Z. Liu, et al., "Metal Nanocrystal Memories - Part I: Device Design and Fabrication." IEEE Transactions on Electron Devices, vol. 49, no. 9, September 2002, pp.1606-1613.

EXAMINER

*hauer**Schulz*

DATE CONSIDERED

*12/25/06*

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.